

[MoB2] Micro-LEDs

Session Date	July 13 (Mon.), 2026
Session Time	14:00–15:45
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Xinqiang Wang (Peking University, China), Dr. Armin Dadgar (Otto-von-Guericke-Universität Magdeburg, Germany)

[MoB2-1] [Invited]

14:00–14:30

In Incorporation and Strain Relaxation for Efficient Red InGaN Micro-LEDs: Towards a RGB Monolithic Approach

A. Dussaigne, J. Bosch, F. Barbier, G. Veux, F. Fedeli, B. Aventurier, D. Cooper, F. Rol, and F. Lévy, CEA-Leti, France

[MoB2-2] [Invited]

14:30–15:00

Enhancing Luminous Efficiency: The Breakthrough of PlayNitride's Tantium® MicroLED

Ching-Liang Lin¹, Yi-Ru Huang², Chia-Yun Kao², and Yun-Li Li¹, ¹Playnitride Inc., Taiwan, ²Playnitride display Co. Ltd., Taiwan

[MoB2-3]

15:00–15:15

GaN-on-Si Single-Chip Full-Color Micro-LED Display

Qian Sun^{1,2}, ¹Suzhou Legin Semiconductor Co., Ltd., China, ²Chinese Academy of Sciences, China

[MoB2-4]

15:15–15:30

Wafer Scale Fabrication of Three-Dimensional InGaN/GaN Nanostructured Quantum Wells for Enhanced Color Controllability of Micro-LEDs

Mandar Kulkarni and Sang-Wan Ryu, Chonnam National University, Korea

Ideal Relaxed InGaN Templates Enabling Ultra-Bright RGB-Emitting MicroLEDs

Zhaoxia Bi^{1,2,3,4}, Magnus Heurlin³, Martin Berg³, Hira Usman¹, Nathanael Löfström^{1,2,3}, Jiawei Sun¹, Anders Gustafsson^{1,2}, Mikael Björk³, and Lars Samuelson^{1,2,3}, ¹Southern University of Science and Technology, China, ²Lund University, Sweden, ³Hexagem AB, Sweden, ⁴Future Display Institute of Xiamen, China